

T495D337K010ATE1007280

T495, Tantalum, MnO2 Tantalum, Commercial Grade, 330 uF, 10%, 10 VDC, SMD, MnO2, Molded, Low ESR, 100 mOhms, 7343, 3.1 mm, 1.3 mm

CATHODE (-) END VIEW



ANODE (+) END VIEW

Dimensions

L

W

н

т s

F

A B

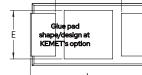
E G

Ρ

R

Х

SIDE VIEW



7.3mm +/-0.3mm

4.3mm +/-0.3mm 2.8mm +/-0.3mm

1.3mm +/-0.3mm

2.4mm +/-0.1mm 3.6mm MIN

0.5mm +/-0.15mm

0.1mm +/-0.1mm REF

3.5mm REF

3.5mm REF

0.9mm REF

1mm REF

0.13mm REF

Click here for the 3D model.

General Information	
Series	T495
Dielectric	MnO2 Tantalum
Style	SMD Chip
Description	SMD, MnO2, Molded, Low ESR
Features	Low ESR
RoHS	Yes
Termination	Tin
AEC-Q200	No
Typical Component Weight	446.84 mg
Shelf Life	156 Weeks
MSL	1

Specifications	
Capacitance	330 uF
Tolerance	10%
Voltage DC	10 VDC (85C), 6.7 VDC (125C)
Temperature Range	-55/+125°C
Rated Temperature	85°C
Dissipation Factor	8% 120Hz 25C
Failure Rate	N/A
ESR	100 mOhms (100kHz 25C)
Ripple Current	1225 mA (rms, 100kHz 25C), 1102.5 mA (rms, 85C), 490 mA (rms, 125C)
Leakage Current	33 uA (5min 25°C)

Packaging Specifications	
Packaging	T&R, 330mm
Packaging Quantity	2500

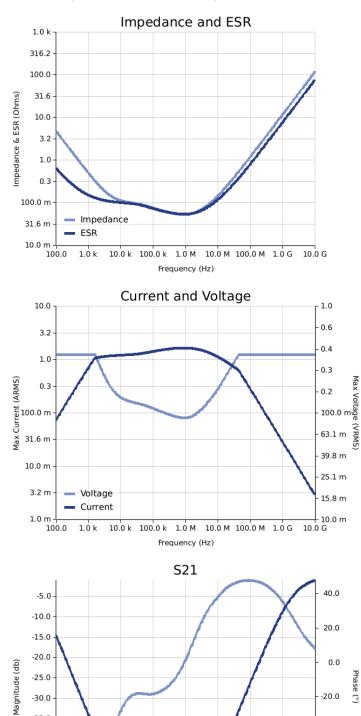
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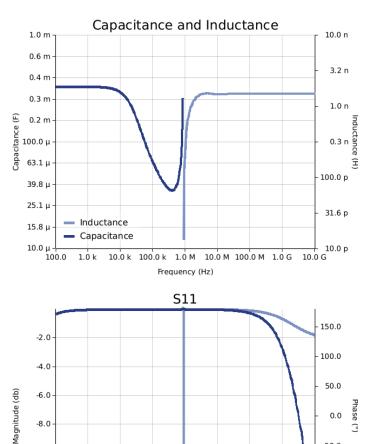


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Simulations

For the complete simulation environment please visit K-SIM.





1.0 k 10.0 k 100.0 k 1.0 M 10.0 M 100.0 M 1.0 G

Frequency (Hz)

-8.0

-10.0

-12.0

-14.0

-40.0

-60.0

10.0 k 100.0 k 1.0 M 10.0 M 100.0 M 1.0 G 10.0 G

Frequency (Hz)

100.0

S11 Phase

S11 Magnitude

S21 Phas S21 Magnitude

1.0 k

-35.0

-40.0 -45.0

-50.0

100.0

-50.0

-100.0

-150.0

10.0 G



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These are simulations.

This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.

- The ESR used for http:// Ripple Current/ voltage vs. requertly plots is the ESR at an other temperature.
 The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
 The effects shown herein are based on measured data from a multiple part sample of the parts in question.
 Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.
 The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages
- generated at any other harmonics.
 Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

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If you have any questions please contact K-SIM.